

[Document Name] Specification

[Title of the Invention] A Method Of Manufacturing A Semiconductor Device

[Claims]

1. A method for fabricating a semiconductor device, comprising steps of:
 - 5 forming an amorphous silicon film;
 - contacting and holding a metal element which promotes crystallization of silicon on the surface of said amorphous silicon film;
 - crystallizing said amorphous silicon film by implementing a first heat treatment to obtain a crystal silicon film;
- 10 forming a thermal oxide film on the surface of said crystal silicon film by implementing a second heat treatment in the temperature range of 500°C to 700°C within an atmosphere containing oxygen, hydrogen and fluorine; and
- removing said thermal oxide film.

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